



Atty.
Dkt. No.

M#

Client Ref.

0284163

01F181

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

Applicant: INABA, Satoshi

Appl. No.: 10/042,264

Filing Date: January 11, 2002

Date: July 29, 2003

Page 1 of 1

Examiner: T. DICKEY

Group Art Unit: 2826

U.S. PATENT DOCUMENTS

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
Th	AR 5,583,361	12/1996	Morishita			
Th	BR 5,580,799	12/1996	Funaki			
Th	CR 4,819,043	04/1989	Yazawa et al.			
	DR					
	ER					
	FR					
	GR					
	HR					
	IR					
	JR					
	KR					
	LR					
	MR					
	NR					

FOREIGN PATENT DOCUMENTS

	Document Number	Date MM/YYYY	Country	Inventor Name	English Abstract		Translation Readily Available	
					Enclosed	No	Enclose	No
Th	OR 0 962 988 A2	12/1999	Europe	Higashi et al.	X		X	
Th	PR 60-50960	03/1985	Japan	Katsuhiko	X			X
Th	QR 7-335837	12/1995	Japan	Masabumi	X			X
	RR							
	SR							
	TR							
	UR							
	VR							

OTHER (Including in this order: Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

Th	WR	MIYAMOTO et al., "Pseudo-SOI: P-N-P-Channel-Doped Bulk MOSFET for Low-Voltage High Performance Applications," Electron Devices Meeting, 1998, pages 15.3.1-15.3.4			
Th	XR	MIZUNO, Tomohisa, "Analytical Model for High-Performance Shallow-Junction-Well Transistor (SJET) with a Fully Depleted Channel Structure," IEEE Transaction on Electron Devices, vol. 40, no. 1, January 1993, pages 105-111, XP 002240660			
	YR				
	ZR				

Examiner

Date Considered: 11/1/04

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.



Atty.
Dkt. No.

M#

Client Ref.

0284163

01F181

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

Applicant: INABA, Satoshi

Appln. No.: 10/042,264

Filing Date: January 11, 2002

Examiner: T. DICKEY

Group Art Unit: 2826

Date: September 15, 2003

Page 1 of 1

U.S. PATENT DOCUMENTS

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
	AR					
	BR					
	CR					
	DR					
	ER					
	FR					
	GR					
	HR					
	IR					
	JR					
	KR					
	LR					
	MR					
	NR					

FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS						English Abstract		Translation Readily Available		
		Document Number	Date MM/YYYY	Country	Inventor Name		Enclosed	No	Enclose	No
	OR									
	PR									
	QR									
	RR									
	SR									
	TR									
	UR									
	VR									

OTHER (Including in this order: Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

72	WR	Sze, S. M., "A Wiley-Interscience publication," ISBN 0-471-05661-8, 1981, pgs 464			
	XR				
	YR				
	ZR				
	AAR				
	BBR				
	CCR				

Examiner

Date Considered: 01/06/04

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.